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#### Maximum ratings 1

#### Table 3 **Maximum ratings**

Devenuentev	Cumphel	Values			11	Note /Test condition
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test condition
	I <sub>F</sub>	-	_	8		$T_{c} \leq 145 ^{\circ}\text{C}, D = 1$
Continuous forward current		-	-	11		$T_c \le 125 ^{\circ}\text{C}, D = 1$
		-	-	20		$T_c \leq 25 ^{\circ}\text{C}, D = 1$
Surge-repetitive forward current, sine halfwave <sup>1</sup>	I <sub>F,RM</sub>	-	-	35	A	$T_c = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$
Surge non-repetitive forward	,	-	_	47		$T_c = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$
current, sine halfwave	I <sub>F,SM</sub>	-	-	37		$T_c = 150 ^{\circ}\text{C}, t_p = 10 \text{ms}$
Non-repetitive peak forward current	I <sub>F,max</sub>	-	-	530		$T_c = 25 ^{\circ}\text{C}, t_p = 10 \mu\text{s}$
i <sup>2</sup> t value	∫i²dt	-	-	11	– A <sup>2</sup> s	$T_c = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$
1-t value	JI-at	-	-	6.9	A-S	$T_c = 150 ^{\circ}\text{C}, t_p = 10 \text{ms}$
Repetitive peak reverse voltage	V <sub>RRM</sub>	-	-	650	۷	<i>T<sub>c</sub></i> = 25 °C
Diode dv/dt ruggedness	dv/dt	-	-	150	V/ns	$V_R = 0480 \text{ V}$
Power dissipation	P <sub>tot</sub>	-	-	63	W	$T_c = 25^{\circ}\text{C}, R_{thJC,max}$
Operating and storage temperature	$\begin{bmatrix} T_j \\ T_{stg} \end{bmatrix}$	-55	-	175	°C	-
Mounting torque	_	_	_	70	Ncm	M3 screw

#### **Thermal characteristics** 2

#### Table 4 Thermal characteristics (PG-TO-220-2)

Deremeter	Sumbol	Values			Unit	Note /Test condition	
Parameter			Тур.	Max.	Unit	Note/Test condition	
Thermal resistance, junction- case	$R_{ m thJC}$	-	1.4	2.4		-	
Thermal resistance, junction- ambient	R <sub>thJA</sub>	_	_	62	K/W	leaded	
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s	

<sup>&</sup>lt;sup>1</sup> The surge-repetitive forward current test was performed with 1000 pulses (half-wave rectified sine with the 10 ms period). **Final Datasheet** 3



# 3 Electrical characteristics

### 3.1 Static characteristics

#### Table 5Static characteristics

Devenuetev	C. mahal	Values			11	Nete /Test soudition
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test condition
DC blocking voltage	V <sub>DC</sub>	650	-	_		<i>T<sub>j</sub></i> = 25 °C
Diada famuard valtaga	$V_F$ $-$ 1.25 1.3 $-$ 1.5 $-$	_	1.25	1.35	V	<i>I</i> <sub><i>F</i></sub> = 8 A, <i>T</i> <sub><i>j</i></sub> = 25 °C
Diode forward voltage		-		<i>I</i> <sub><i>F</i></sub> = 8 A, <i>T</i> <sub><i>j</i></sub> = 150 °C		
		-	0.8	27	μΑ	$V_R$ = 420 V, $T_j$ = 25 °C
Reverse current	$I_R$	_	27	_		$V_R$ = 420 V, $T_j$ = 125 °C
		-	62	-		$V_R$ = 420 V, $T_j$ = 150 °C

### 3.2 AC characteristics

#### Table 6AC characteristics

Deveneter	Cumphel	Values			11	Note /Test Condition	
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test Condition	
Total capacitive charge			12.2		2	$V_R$ = 400 V, $T_j$ = 150 °C,	
	Qc	-	12.2	-	nC	di/dt = 200 A/ $\mu$ s, I <sub>F</sub> $\leq$ I <sub>F,MAX</sub>	
	С	_	401	_	pF	$V_R = 1 \text{ V, } f = 1 \text{ MHz,}$	
						<i>T<sub>j</sub></i> = 25 °C	
Total conscitones			24	_		$V_R$ = 300 V, $f$ = 1 MHz,	
Total capacitance		-				<i>T<sub>j</sub></i> = 25 °C	
		-	23			$V_R$ = 600 V, f = 1 MHz,	
				-		<i>T<sub>j</sub></i> = 25 °C	



## 4 Diagrams

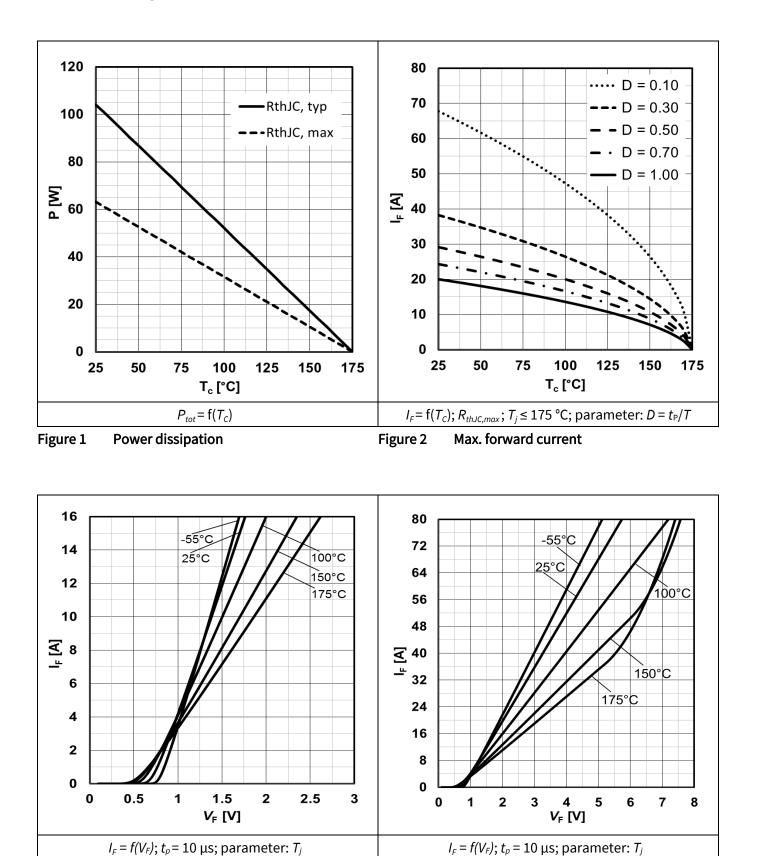


Figure 3 Typ. forward characteristics

Figure 4 Typ. forward characteristics

in surge current

**Final Datasheet** 

### 6<sup>th</sup> Generation CoolSiC<sup>™</sup> IDH08G65C6

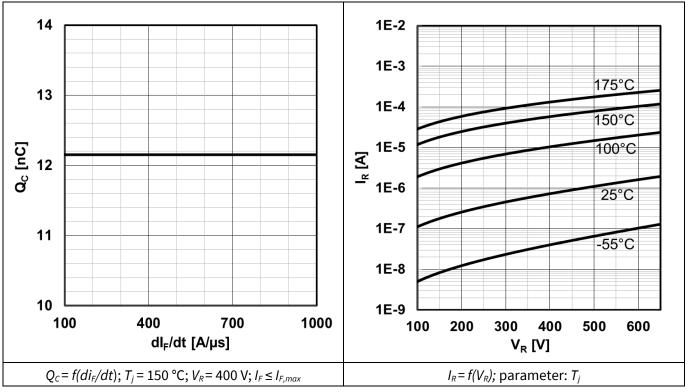
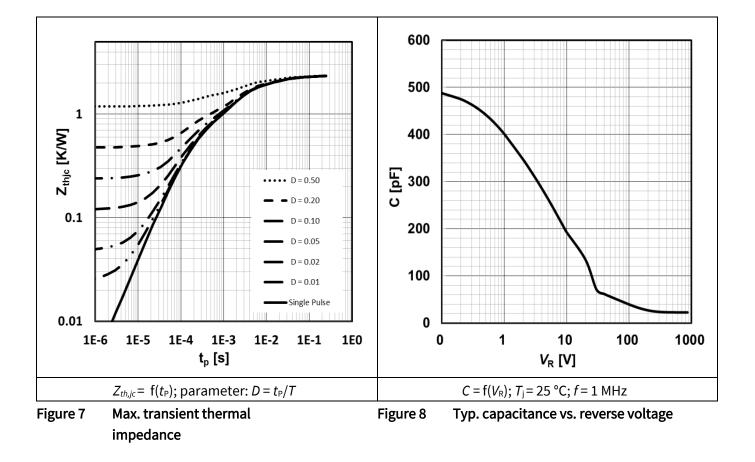


Figure 5 Typ. cap. charge vs. current slope

Figure 6 Typ. reverse current vs. reverse voltage



Final Datasheet



## 6<sup>th</sup> Generation CoolSiC<sup>™</sup> IDH08G65C6



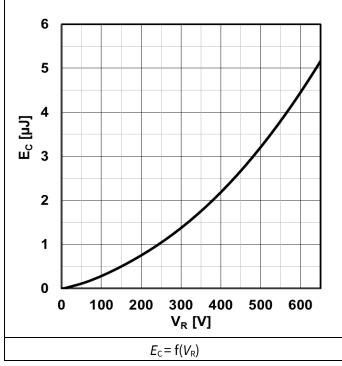
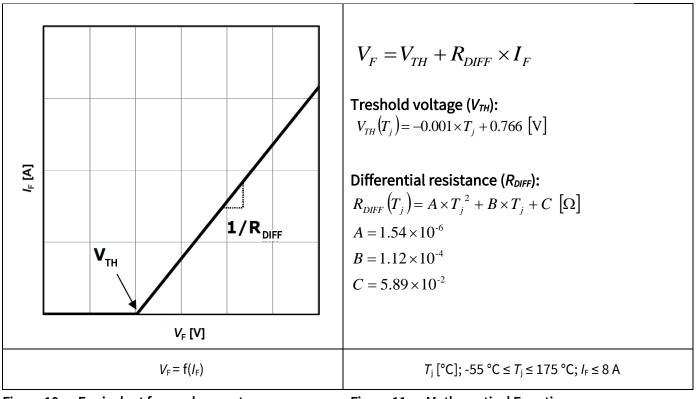


Figure 9 Typ. capacitance stored energy

# 5 Simplified forward characteristic



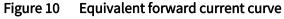


Figure 11 Mathematical Equation



#### **Package outlines** 6

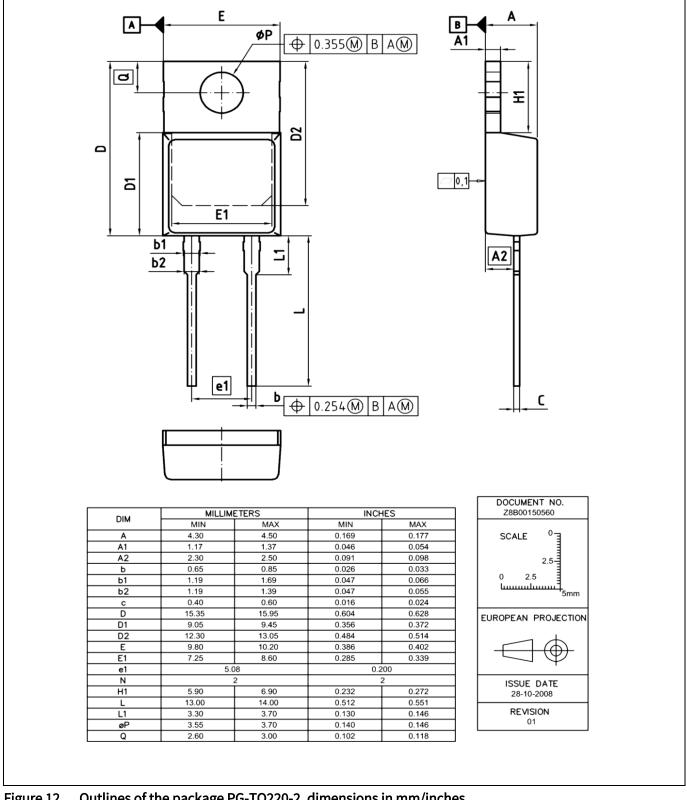


Figure 12 Outlines of the package PG-TO220-2, dimensions in mm/inches

IDH08G65C6



### **Revision History**

### Major changes since the last revision

Revision	Date	Subject (major changes since last revision)	
2.0	2017-05-23	Release of final version	

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